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AOD4S60

600V 4A αMOS™ Power Transistor

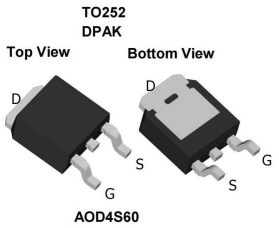
General Description

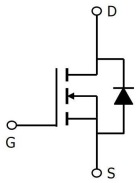
The AOD4S60 have been fabricated using the advanced αMOS™ high voltage process that is designed to deliver high levels of performance and robustness in switching applications. By providing low $R_{DS(on)}$, Q_g and E_{OSS} along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

Product Summary

V_{DS} @ $T_{j,max}$	700V
I_{DM}	16A
$R_{DS(ON),max}$	0.9Ω
$Q_{g,typ}$	6nC
E_{oss} @ 400V	1.5μJ

100% UIS Tested
100% R_g Tested





Orderable Part Number	Package Type	Form	Minimum Order Quantity
	TO-252	Tape & Reel	2500

Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current	T_C=25℃	I_D	4	A
	T_C=100℃		3	
Pulsed Drain Current [C]		I_{DM}	16	
Avalanche Current [C]		I_{AR}	1.6	A
Repetitive avalanche energy [C]		E_{AR}	38	mJ
Single pulsed avalanche energy [H]		E_{AS}	77	mJ
Power Dissipation [B]	T_C=25℃	P_D	56.8	W
	Derate above 25°C		0.45	W/ °C
MOSFET dv/dt ruggedness		dv/dt	100	V/ns
Peak diode recovery dv/dt			20	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	℃
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds [K]		T_L	300	℃

Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Units
Maximum Junction-to-Ambient [A,D]	$R_{\theta JA}$	45	55	℃/W
Maximum Case-to-sink [A]	$R_{\theta CS}$	--	0.5	℃/W
Maximum Junction-to-Case [D,F]	$R_{\theta JC}$	1.8	2.2	℃/W

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Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA, V_{GS}=0V, T_J=25℃	600	-	-	V
		I_D=250μA, V_{GS}=0V, T_J=150℃	650	700	-	
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=600V, V_{GS}=0V	-	-	1	μA
		V_{DS}=480V, T_J=150℃	-	10	-	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±30V	-	-	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=5V,I_D=250μA	2.9	3.5	4.1	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=2A, T_J=25℃	-	0.78	0.9	Ω
		V_{GS}=10V, I_D=2A, T_J=150℃	-	2	2.4	Ω
V_{SD}	Diode Forward Voltage	I_S=2A,V_{GS}=0V, T_J=25℃	-	0.81	-	V
I_S	Maximum Body-Diode Continuous Current		-	-	4	A
I_{SM}	Maximum Body-Diode Pulsed Current[C]		-	-	16	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz	-	263	-	pF
C_{oss}	Output Capacitance		-	21	-	pF
$C_{o(er)}$	Effective output capacitance, energy related[I]	V_{GS}=0V, V_{DS}=0 to 480V, f=1MHz	-	17.1	-	pF
$C_{o(tr)}$	Effective output capacitance, time related[J]		-	47.7	-	pF
C_{rss}	Reverse Transfer Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz	-	0.75	-	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	-	18	-	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=480V, I_D=2A	-	6	-	nC
Q_{gs}	Gate Source Charge		-	1.6	-	nC
Q_{gd}	Gate Drain Charge		-	1.8	-	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=400V, I_D=2A, R_G=25Ω	-	18	-	ns
t_r	Turn-On Rise Time		-	8	-	ns
$t_{D(off)}$	Turn-Off DelayTime		-	40	-	ns
t_f	Turn-Off Fall Time		-	12	-	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=2A,dI/dt=100A/μs,V_{DS}=400V	-	177	-	ns
I_{rm}	Peak Reverse Recovery Current	I_F=2A,dI/dt=100A/μs,V_{DS}=400V	-	12	-	A
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=2A,dI/dt=100A/μs,V_{DS}=400V	-	1.5	-	μC

A. The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A=25℃.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150℃, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150℃, Ratings are based on low frequency and duty cycles to keep initial T_J =25℃.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150℃. The SOA curve provides a single pulse ratin g.

G.These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25℃.

H. L=60mH, I_{AS}=1.6A, V_{DD}=150V, Starting T_J=25℃

I. $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.

J. $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.

K. Wave soldering only allowed at leads.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

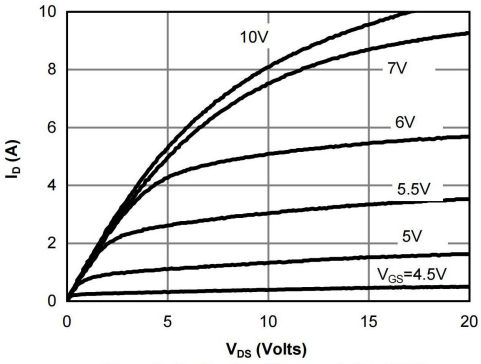


Figure 1: On-Region Characteristics@25℃

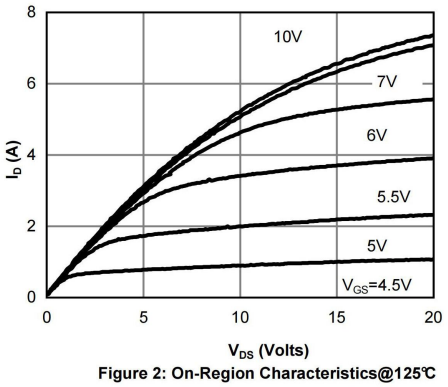


Figure 2: On-Region Characteristics@125℃

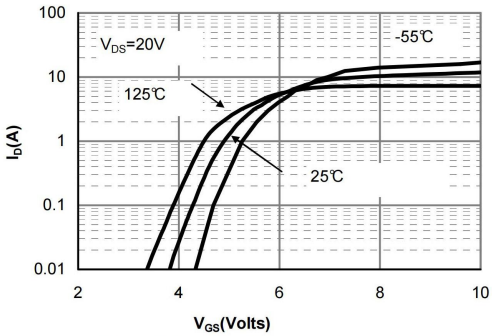


Figure 3: Transfer Characteristics

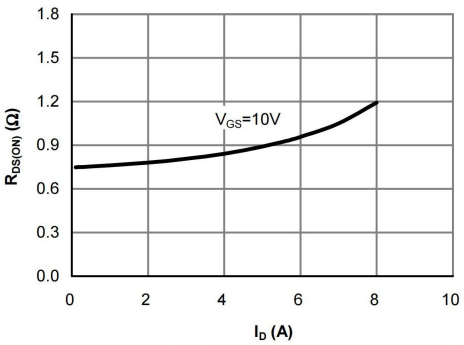


Figure 4: On-Resistance vs. Drain Current and Gate Voltage

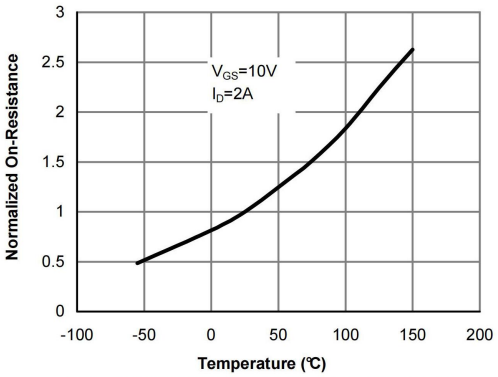


Figure 5: On-Resistance vs. Junction Temperature

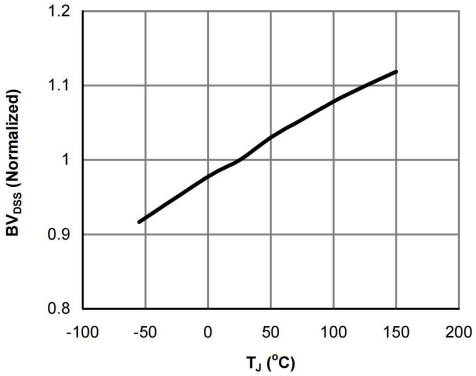


Figure 6: Break Down vs. Junction Temperature

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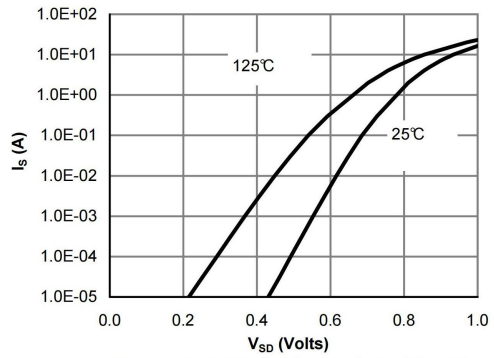


Figure 7: Body-Diode Characteristics (Note E)

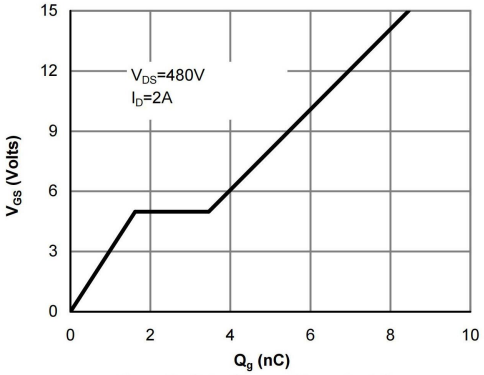


Figure 8: Gate-Charge Characteristics

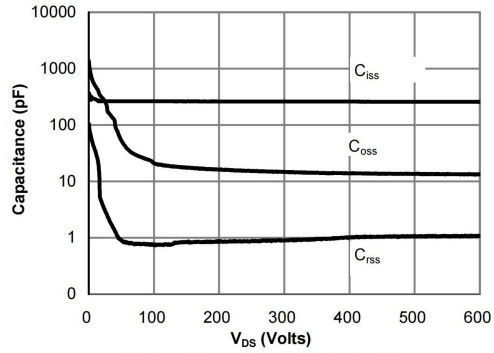


Figure 9: Capacitance Characteristics

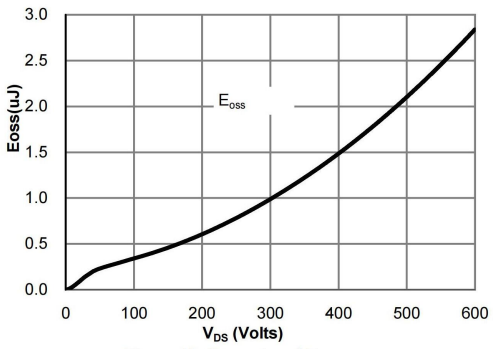


Figure 10: Coss stored Energy

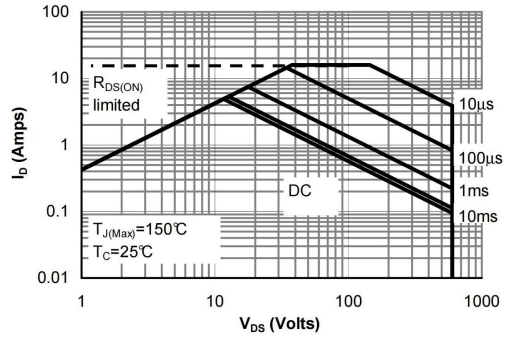


Figure 11: Maximum Forward Biased Safe Operating Area (Note F)

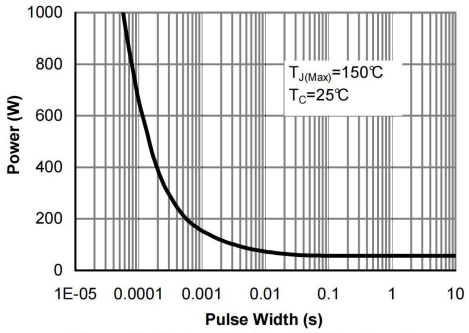


Figure 12: Single Pulse Power Rating Junction-to-Case (Note F)

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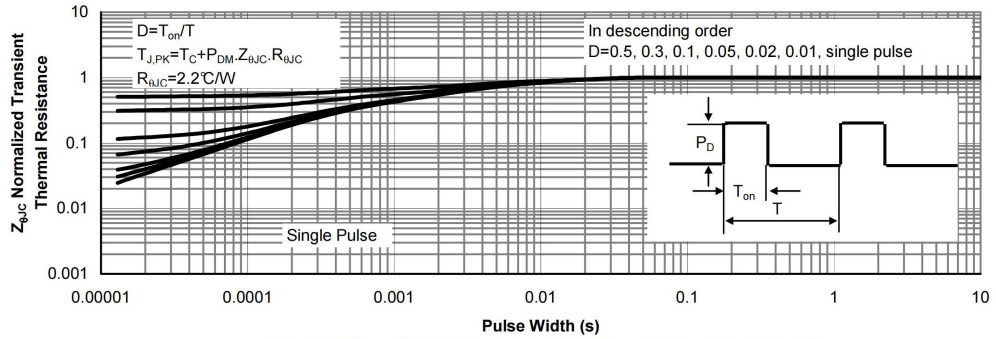


Figure 13: Normalized Maximum Transient Thermal Impedance (Note F)

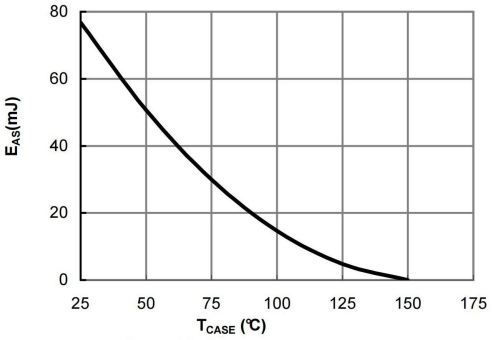


Figure 14: Avalanche energy

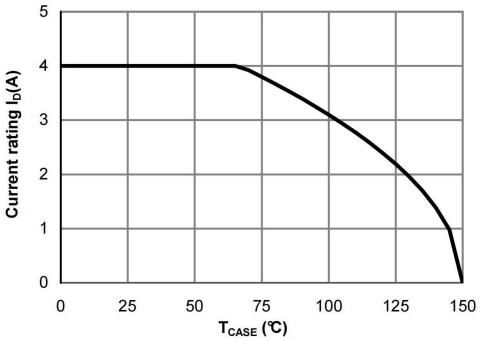


Figure 15: Current De-rating (Note B)

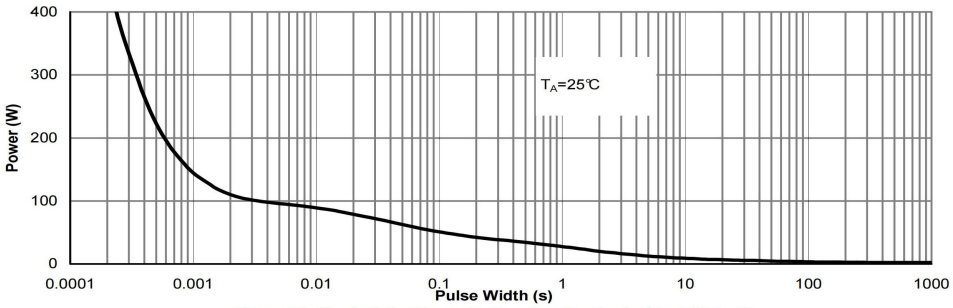


Figure 16: Single Pulse Power Rating Junction-to-Ambient (Note G)

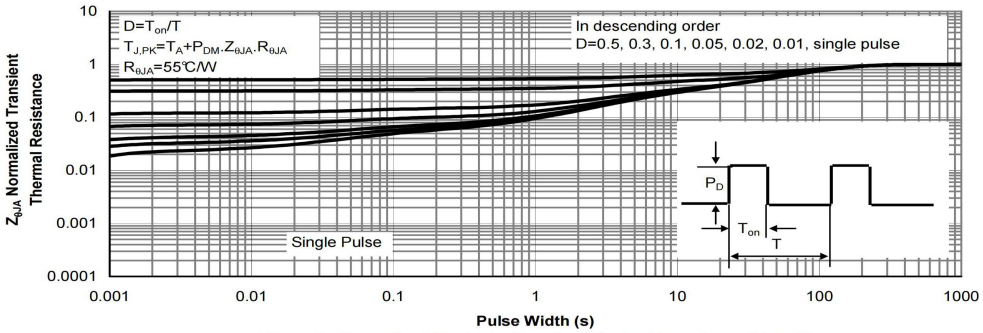
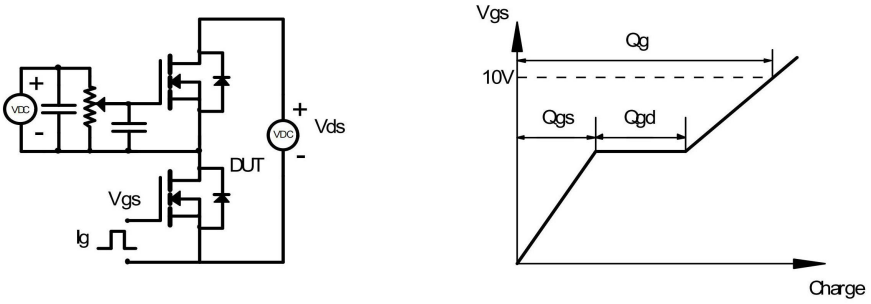


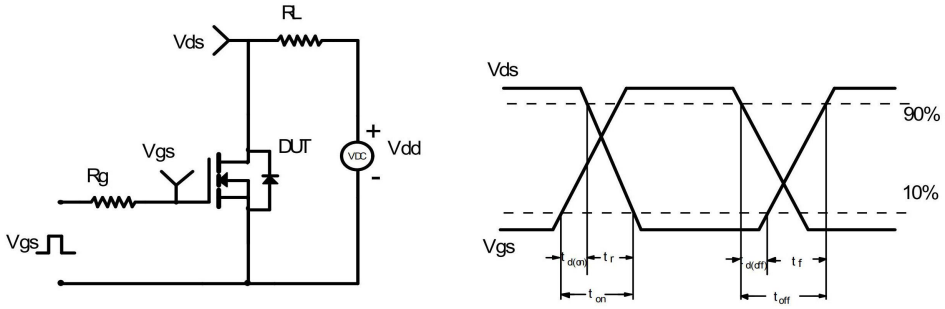
Figure 17: Normalized Maximum Transient Thermal Impedance (Note G)

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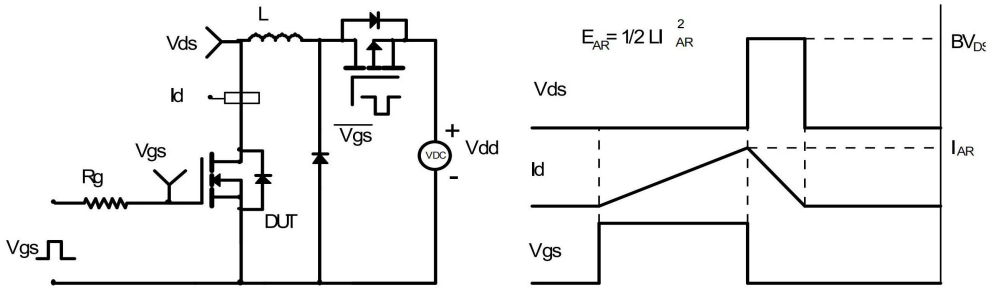
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

